

Zener Diodes, 24 and 40 Watt Peak Power

SOT-23 Dual Common Anode Zeners



ON Semiconductor®

www.onsemi.com

MMBZHxxxALT1G Series, SZMMBZHxxxALT1G Series

These dual monolithic silicon Zener diodes are designed for applications requiring transient overvoltage ESD protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Features

- SOT-23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Standard Zener Breakdown Voltage Range – 5.6 V to 47 V
- Peak Power – 24 or 40 W @ 1.0 ms (Unidirectional), per Figure 6 Waveform
- ESD Rating:
 - Class 3B (> 16 kV) per the Human Body Model
 - Class C (> 400 V) per the Machine Model
 - IEC61000-4-2 Level 4, ±30 kV Contact Discharge
- Low Leakage < 5.0 µA
- Flammability Rating UL 94 V-0
- 175°C T_{J(MAX)} – Rated for High Temperature, Mission Critical Applications
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Mechanical Characteristics

CASE: Void-free, transfer-molded, thermosetting plastic case

FINISH: Corrosion resistant finish, easily solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:

260°C for 10 Seconds

Package designed for optimal automated board assembly

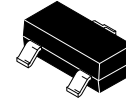
Small package size for high density applications

Available in 8 mm Tape and Reel

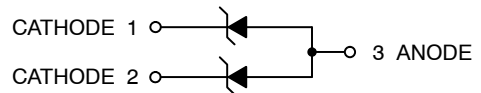
Use the Device Number to order the 7 inch/3,000 unit reel.

Replace the “T1” with “T3” in the Device Number to order the

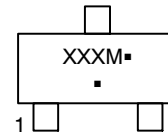
13 inch/10,000 unit reel.



SOT-23
CASE 318
STYLE 12



MARKING DIAGRAM



XXX = Specific Device Code

M = Date Code

▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the table on page 3 of this data sheet.

MMBZHxxxALT1G Series, SZMMBZHxxxALT1G Series

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 1.0 ms (Note 1) MMBZH5V6ALT1G thru MMBZH9V1ALT1G @ $T_L \leq 25^\circ\text{C}$ MMBZH12VALT1G thru MMBZH47VALT1G	P_{pk}	24 40	W
Total Power Dissipation on FR-5 Board (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.5	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	540	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to +175	$^\circ\text{C}$
Lead Solder Temperature - Maximum (10 Second Duration)	T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Non-repetitive current pulse per Figure 6 and derate above $T_A = 25^\circ\text{C}$ per Figure 7.
2. FR-5 = 1.0 x 0.75 x 0.62 in.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBZHxVxALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZMMBZHxVxALT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZHxVxALT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SZMMBZHxVxALT3G*	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBZHxxVxALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZMMBZHxxVxALT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZHxxVxALT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SZMMBZHxxVxALT3G*	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

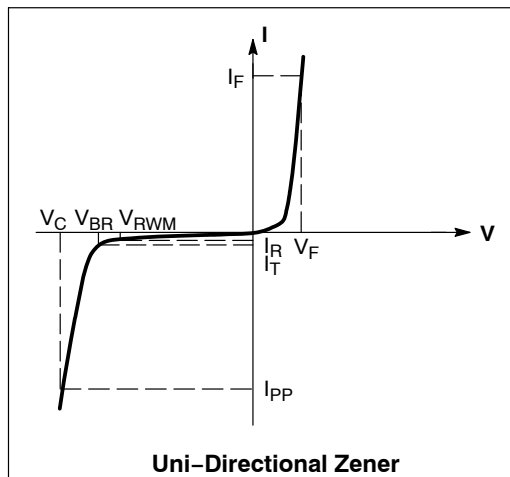
MMBZHxxxALT1G Series, SZMMBZHxxxALT1G Series

ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
ΘV_{BR}	Maximum Temperature Coefficient of V_{BR}
I_F	Forward Current
V_F	Forward Voltage @ I_F
Z_{ZT}	Maximum Zener Impedance @ I_{ZT}
I_{ZK}	Reverse Current
Z_{ZK}	Maximum Zener Impedance @ I_{ZK}



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

($V_F = 0.9\text{ V Max @ } I_F = 10\text{ mA}$) (5% Tolerance)

24 WATTS

Device*	Device Marking	V_{RWM} Volts	$I_R @ V_{RWM}$ μA	Breakdown Voltage				Max Zener Impedance (Note 4)			$V_C @ I_{PP}$ (Note 5)		ΘV_{BR} $\text{mV}/^\circ\text{C}$
				V_{BR} (Note 3) (V)			@ I_T mA	Z_{ZT} @ I_{ZT} Ω	Z_{ZK} @ I_{ZK} Ω	mA	V_C V	I_{PP} A	
				Min	Nom	Max							
MMBZH5V6ALT1G**	5A6	3.0	5.0	5.32	5.6	5.88	20	11	1600	0.25	8.0	3.0	1.26
MMBZH6V2ALT1G**	6A2	3.0	0.5	5.89	6.2	6.51	1.0	-	-	-	8.7	2.76	2.80
MMBZH6V8ALT1G**	6A8	4.5	0.5	6.46	6.8	7.14	1.0	-	-	-	9.6	2.5	3.4
MMBZH9V1ALT1G**	9A1	6.0	0.3	8.65	9.1	9.56	1.0	-	-	-	14	1.7	7.5

($V_F = 0.9\text{ V Max @ } I_F = 10\text{ mA}$) (5% Tolerance)

40 WATTS

Device*	Device Marking	V_{RWM} Volts	$I_R @ V_{RWM}$ nA	Breakdown Voltage				$V_C @ I_{PP}$ (Note 5)		ΘV_{BR} $\text{mV}/^\circ\text{C}$
				V_{BR} (Note 3) (V)			@ I_T mA	V_C V	I_{PP} A	
				Min	Nom	Max				
MMBZH12VALT1G**	12A	8.5	200	11.40	12	12.60	1.0	17	2.35	7.5
MMBZH15VALT1G**	15A	12	50	14.25	15	15.75	1.0	21	1.9	12.3
MMBZH16VALT1G**	16A	13	50	15.20	16	16.80	1.0	23	1.7	13.8
MMBZH18VALT1G	ACJ	14.5	50	17.10	18	18.90	1.0	25	1.6	15.3
MMBZH20VALT1G**	20A	17	50	19.00	20	21.00	1.0	28	1.4	17.2
MMBZH27VALT1G**	27A	22	50	25.65	27	28.35	1.0	40	1.0	24.3
MMBZH33VALT1G**	33A	26	50	31.35	33	34.65	1.0	46	0.87	30.4
MMBZH47VALT1G**	47A	38	50	44.65	47	49.35	1.0	54	0.74	43.1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C .

4. Z_{ZT} and Z_{ZK} are measured by dividing the AC voltage drop across the device by the AC current applied. The specified limits are for $I_{Z(AC)} = 0.1 I_{Z(DC)}$, with the AC frequency = 1.0 kHz.

5. Surge current waveform per Figure 6 and derate per Figure 7

* Includes SZ-prefix devices where applicable.

**AEC-Q release available upon request.

MMBZHxxxALT1G Series, SZMMBZHxxxALT1G Series

TYPICAL CHARACTERISTICS

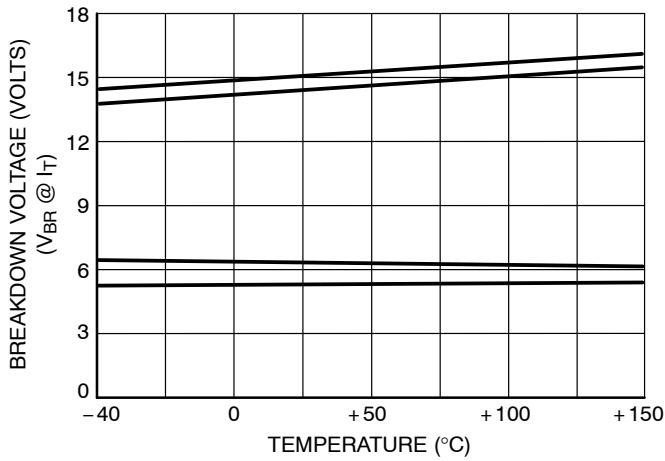


Figure 1. Typical Breakdown Voltage versus Temperature

(Upper curve for each voltage is bidirectional mode, lower curve is unidirectional mode)

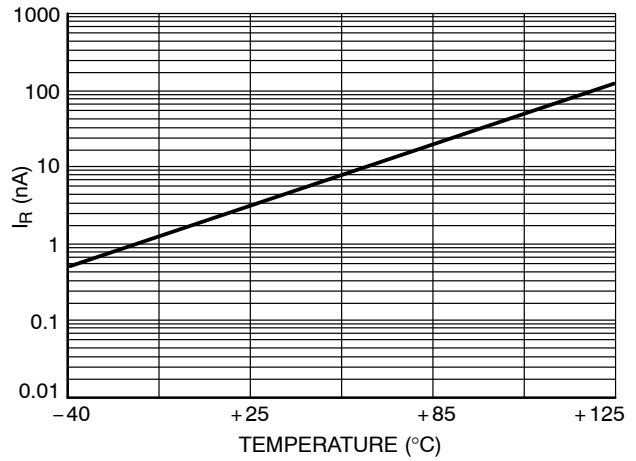


Figure 2. Typical Leakage Current versus Temperature

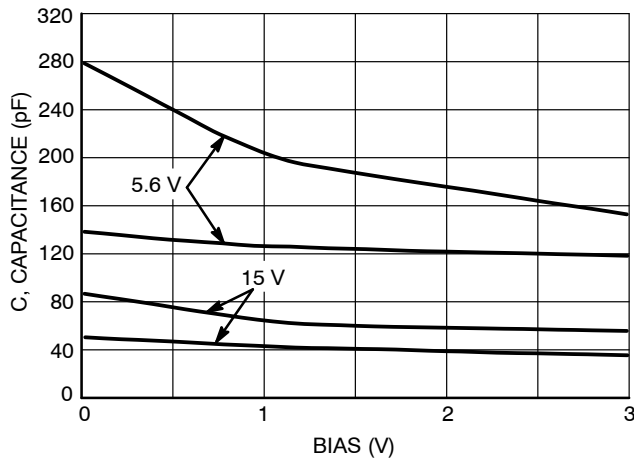


Figure 3. Typical Capacitance versus Bias Voltage

(Upper curve for each voltage is unidirectional mode, lower curve is bidirectional mode)

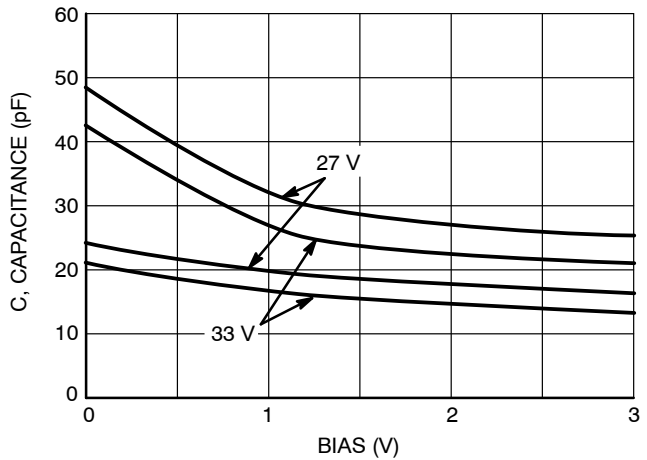


Figure 4. Typical Capacitance versus Bias Voltage

(Upper curve for each voltage is unidirectional mode, lower curve is bidirectional mode)

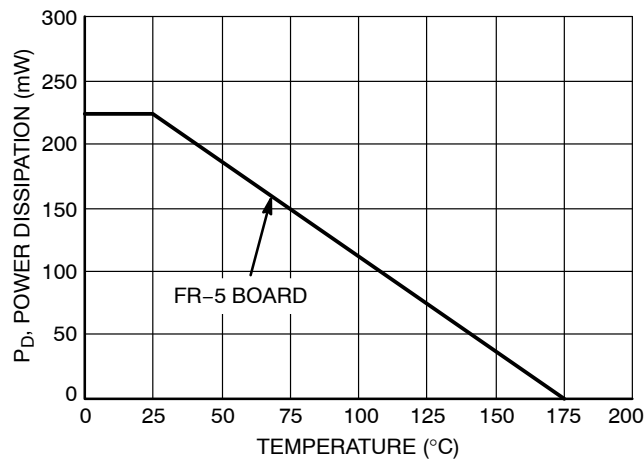


Figure 5. Steady State Power Derating Curve

MMBZHxxxALT1G Series, SZMMBZHxxxALT1G Series

TYPICAL CHARACTERISTICS

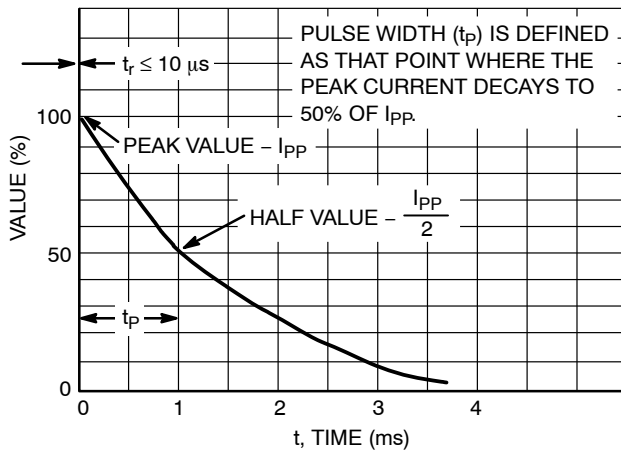


Figure 6. Pulse Waveform

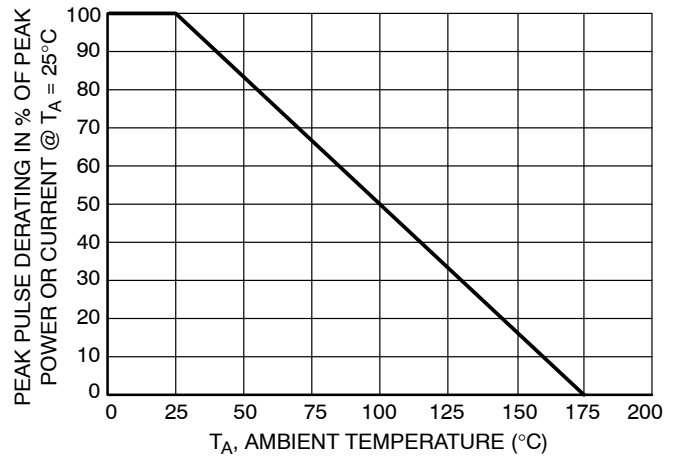


Figure 7. Pulse Derating Curve

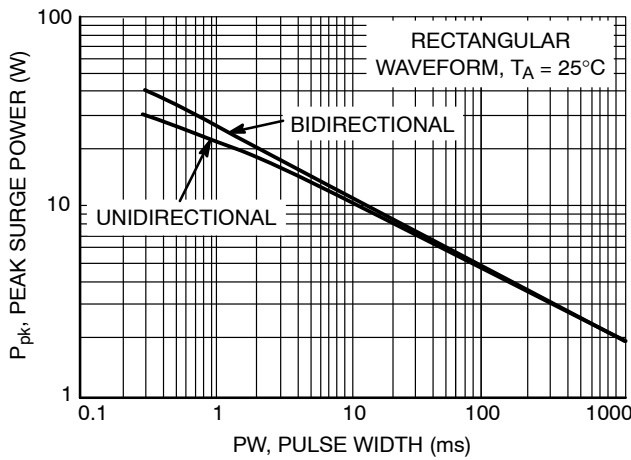


Figure 8. Maximum Non-repetitive Surge Power, P_{pk} versus PW

Power is defined as $V_{RSM} \times I_Z(pk)$ where V_{RSM} is the clamping voltage at $I_Z(pk)$.

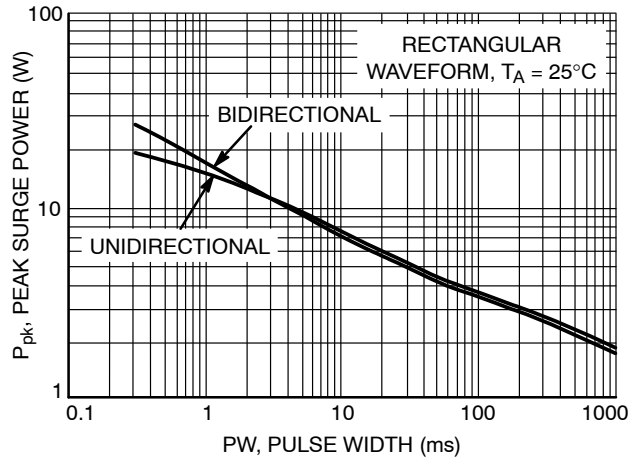


Figure 9. Maximum Non-repetitive Surge Power, $P_{pk}(NOM)$ versus PW

Power is defined as $V_Z(NOM) \times I_Z(pk)$ where $V_Z(NOM)$ is the nominal Zener voltage measured at the low test current used for voltage classification.

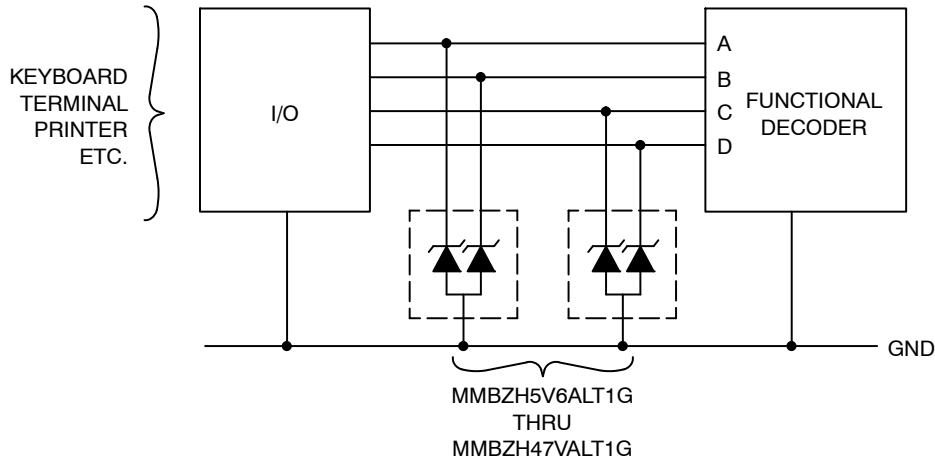
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TYPICAL COMMON ANODE APPLICATIONS

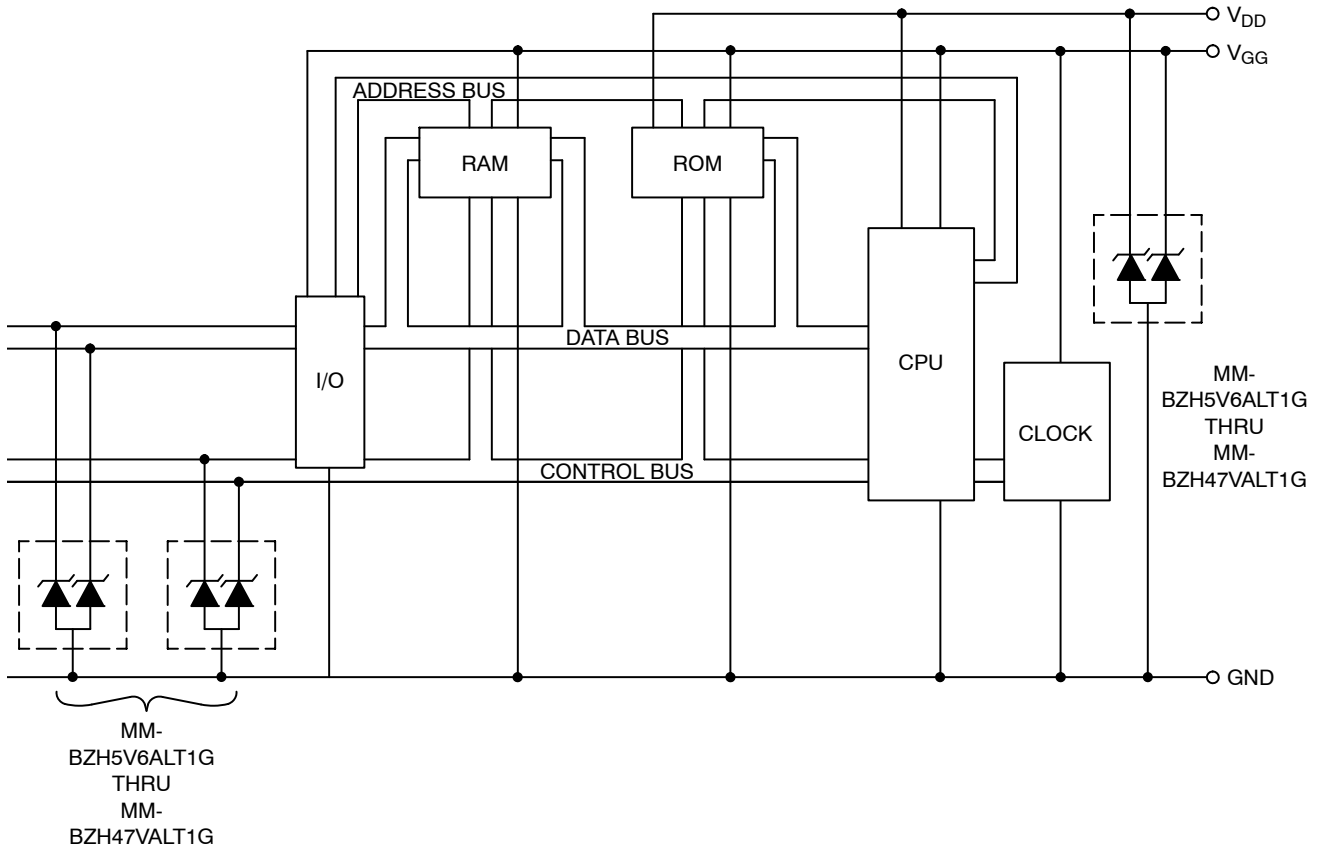
A dual junction common anode design in a SOT-23 package protects two separate lines using only one package. This adds flexibility and creativity to PCB design especially

when board space is at a premium. Two simplified examples of ESD applications are illustrated below.

Computer Interface Protection



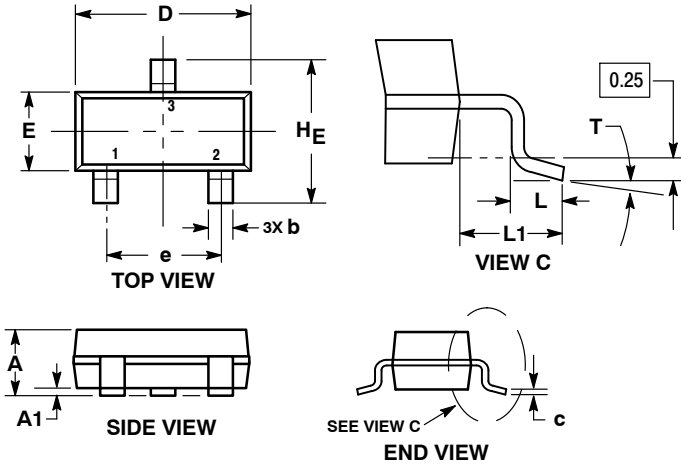
Microprocessor Protection



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PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AS



NOTES:

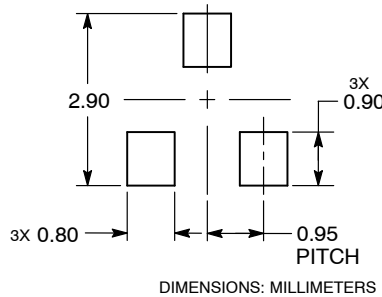
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

STYLE 12:

1. CATHODE
2. CATHODE
3. ANODE

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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